

Kinam Kim

List of Publications by Year in descending order

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Version: 2024-02-01

25
papers

4,447
citations

840776

11
h-index

996975

15
g-index

26
all docs

26
docs citations

26
times ranked

7035
citing authors

#	ARTICLE	IF	CITATIONS
1	Neuromorphic electronics based on copying and pasting the brain. Nature Electronics, 2021, 4, 635-644.	26.0	94
2	The Smallest Engine Transforming Humanity: The Past, Present, and Future. , 2021, , .		21
3	17.1 A 10nm FinFET 128Mb SRAM with assist adjustment system for power, performance, and area optimization. , 2016, , .		28
4	1.1 Silicon technologies and solutions for the data-driven world. , 2015, , .		44
5	Three-Dimensional 128 Gb MLC Vertical nand Flash Memory With 24-WL Stacked Layers and 50 MB/s High-Speed Programming. IEEE Journal of Solid-State Circuits, 2015, 50, 204-213.	5.4	167
6	Is quantum capacitance in graphene a potential hurdle for device scaling?. Nano Research, 2014, 7, 453-461.	10.4	9
7	Highly sensitive and reliable X-ray detector with HgI ₂ photoconductor and oxide drive TFT. , 2011, , .		4
8	Dual gate photo-thin film transistor with high photoconductive gain for high reliability, and low noise flat panel transparent imager. , 2011, , .		4
9	A fast, high-endurance and scalable non-volatile memory device made from asymmetric Ta ₂ O ₅ /TaO ₂ bilayer structures. Nature Materials, 2011, 10, 625-630.	27.5	1,930
10	A role for graphene in silicon-based semiconductor devices. Nature, 2011, 479, 338-344.	27.8	667
11	Full-colour quantum dot displays fabricated by transfer printing. Nature Photonics, 2011, 5, 176-182.	31.4	997
12	Nearly single-crystalline GaN light-emitting diodes on amorphous glass substrates. Nature Photonics, 2011, 5, 763-769.	31.4	156
13	A VISION OF FRAM AS A FUSION MEMORY. Integrated Ferroelectrics, 2008, 96, 100-111.	0.7	6
14	A 60nm 6Gb/s/pin GDDR5 Graphics DRAM with Multifaceted Clocking and ISI/SSN-Reduction Techniques. , 2008, , .		19
15	A 0.1- μm 1.8-V 256-Mb Phase-Change Random Access Memory (PRAM) With 66-MHz Synchronous Burst-Read Operation. IEEE Journal of Solid-State Circuits, 2007, 42, 210-218.	5.4	119
16	Integration of lead zirconium titanate thin films for high density ferroelectric random access memory. Journal of Applied Physics, 2006, 100, 051604.	2.5	89
17	Twin SONOS Memory With 30-nm Storage Nodes Under a Merged Gate Fabricated With Inverted Sidewall and Damascene Process. IEEE Electron Device Letters, 2004, 25, 317-319.	3.9	22
18	Effect of the Bottom Electrode Contact (BEC) on the phase transformation of N ₂ -doped Ge ₂ Sb ₂ Te ₅ (N-GST) in a Phase-change Random Access Memory. Materials Research Society Symposia Proceedings, 2004, 830, 25.	0.1	5

#	ARTICLE	IF	CITATIONS
19	Electrical properties of highly reliable plug buffer layer for high-density ferroelectric memory. Applied Physics Letters, 2002, 80, 2377-2379.	3.3	11
20	Guest editorial special section on issues related to semiconductor manufacturing at technology nodes below 70 nm. IEEE Transactions on Semiconductor Manufacturing, 2002, 15, 133-136.	1.7	2
21	Dielectric loss peak due to platinum electrode porosity in lead zirconate titanate thin-film capacitors. Applied Physics Letters, 2002, 81, 2436-2438.	3.3	23
22	A novel multi-channel field effect transistor (McFET) on bulk Si for high performance sub-80nm application. , 0, , .		11
23	A 0.18 μ m 3.0 V 64 Mb non-volatile phase-transition random-access memory (PRAM). , 0, , .		7
24	Enhanced data retention of damascene-finFET DRAM with local channel implantation and $>100\times$ fin surface orientation engineering. , 0, , .		10
25	Enhanced write performance of a 64Mb phase-change random access memory. , 0, , .		2